

GJ1182

PNP SILICON EPITAXIAL PLANAR TRANSISTOR

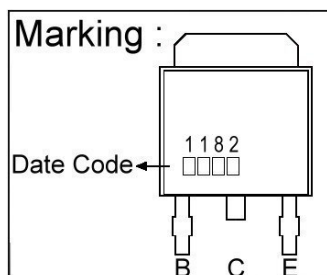
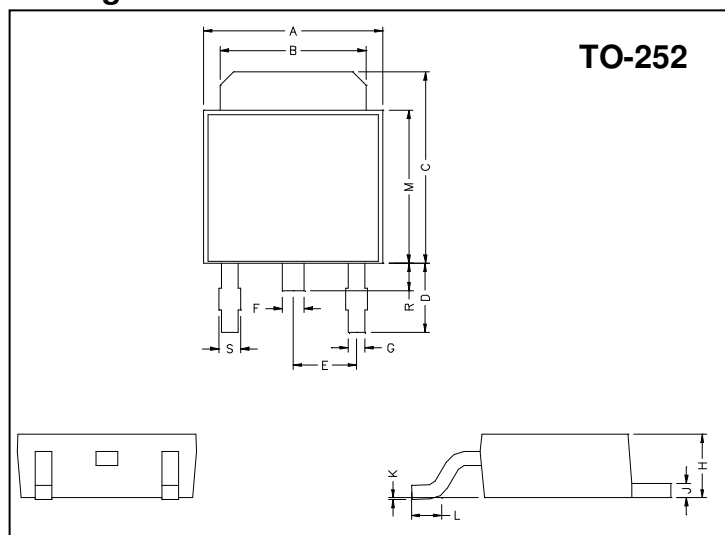
Description

The GJ1182 is designed for medium power amplifier applications.

Features

- Low collector saturation voltage : $V_{CE(sat)} = -0.5V$ (Typ.)

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55~+150	$^\circ C$
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Collector Current (Pulse, $P_w=100ms$)	I_C	-3	A
Total Power Dissipation($T_c=25^\circ C$)	P_D	10	W

Electrical Characteristics ($T_a = 25^\circ C$, unless otherwise noted)

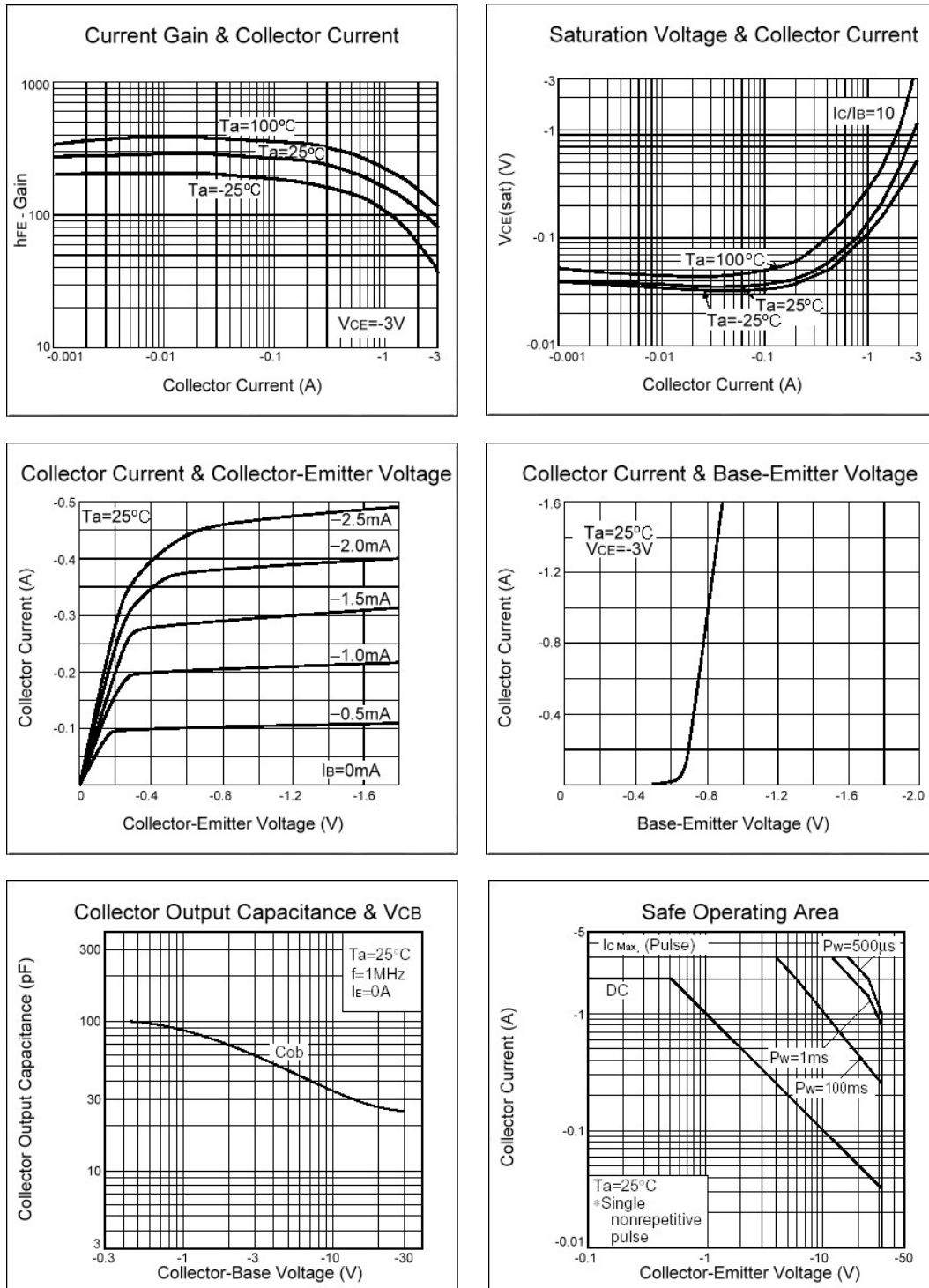
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CBO}	-40	-	-	V	$I_C = -50\mu A$, $I_E = 0$
V_{CEO}	-32	-	-	V	$I_C = -1mA$, $I_B = 0$
V_{EBO}	-5	-	-	V	$I_E = -50\mu A$, $I_C = 0$
I_{CBO}	-	-	-1	μA	$V_{CB} = -20V$, $I_E = 0$
I_{EBO}	-	-	-1	μA	$V_{EB} = -4V$, $I_C = 0$
$*V_{CE(sat)}$	-	-500	-800	mV	$I_C = -2A$, $I_B = -200mA$
$*h_{FE}$	82	-	390		$V_{CE} = -3V$, $I_C = -500mA$
f_T	-	100	-	MHz	$V_{CE} = -5V$, $I_C = -500mA$, $f = 100MHz$
C_{ob}	-	50	-	pF	$V_{CB} = -10V$, $I_E = 0$, $f = 1MHz$

* Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE}

Rank	P	Q	R
Range	82 ~ 180	120 ~ 270	180 ~ 390

Characteristics Curve



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